# SLOVENSKI STANDARD
# oSIST prEN IEC 60749-23:2025

**01-januar-2025**

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**Polprevodniški elementi - Metode za mehansko in klimatsko preskušanje - 23. del: Obratovalna življenjska doba pri visoki temperaturi**

Semiconductor devices - Mechanical and climatic test methods - Part 23: High temperature operating life

Halbleiterbauelemente - Mechanische und klimatische Prüfverfahren - Teil 23: Lebensdauer bei hoher Temperatur

Dispositifs à semiconducteurs - Méthodes d'essais mécaniques et climatiques - Partie 23: Durée de vie en fonctionnement à haute température



**Ta slovenski standard je istoveten z:** **prEN IEC 60749-23:2024**



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**ICS:**

| | | |
|---|---|---|
| 31.080.01 | Polprevodniški elementi (naprave) na splošno | Semiconductor devices in general |

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# 47/2881/CDV

COMMITTEE DRAFT FOR VOTE (CDV)

| | |
|---|---|
| PROJECT NUMBER: **IEC 60749-23 ED2** | |
| DATE OF CIRCULATION: **2024-11-22** | CLOSING DATE FOR VOTING: **2025-02-14** |
| SUPERSEDES DOCUMENTS: **47/2879/RR** | |

| IEC TC 47 : SEMICONDUCTOR DEVICES | |
|---|---|
| SECRETARIAT: Korea, Republic of | SECRETARY: Mr Cheolung Cha |
| OF INTEREST TO THE FOLLOWING COMMITTEES: TC 91,TC 104 | HORIZONTAL FUNCTION(S): |
| ASPECTS CONCERNED: | |
| ☐ SUBMITTED FOR CENELEC PARALLEL VOTING | ☒ NOT SUBMITTED FOR CENELEC PARALLEL VOTING |



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TITLE:

**Semiconductor devices - Mechanical and climatic test methods - Part 23: High temperature operating life**

PROPOSED STABILITY DATE: 2025

NOTE FROM TC/SC OFFICERS:

# CONTENTS

INTERNATIONAL ELECTROTECHNICAL COMMISSION

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# SEMICONDUCTOR DEVICES – MECHANICAL AND CLIMATIC TEST METHODS –

## Part 23: High temperature operating life

## FOREWORD

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This edition includes the following significant technical changes with respect to the previous edition:

a) Absolute stress test definitions and resultant test durations have been updated.

The text of this International Standard is based on the following documents:

| Draft | Report on voting |
|---|---|
| XX/XX/FDIS | XX/XX/RVD |

Full information on the voting for its approval can be found in the report on voting indicated in the above table.

The language used for the development of this International Standard is English.

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